NSN 5962-01-355-3766

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View Online at https://aerobasegroup.com/nsn/5962-01-355-3766				
Overall Length:				
0.540 inches				
Overall Height:				
Between 0.045 inches and 1.000 inches				
Overall Width:				
Between 0.745 inches and 1.040 inches				
Body Length:				
0.540 inches				
Body Width:				
Between 0.245 inches and 0.300 inches				
Body Height:				
Between 0.045 inches and 0.100 inches				
Maximum Power Dissipation Rating:				
1.0 watts				
Operating Tempurature Range:				
-55.0/+125.0 degrees celsius				
Storage Tempurature Range:				
-65.0/+150.0 degrees celsius				
Features Provided:				
Monolithic and programmable and bidirectional and electrostatic sensitive				
Inclosure Material:				
Ceramic				
Inclosure Configuration:				
Flat pack				
Output Logic Form:				
Transistor-transistor logic				
Input Circuit Pattern:				
16 input				
Case Outline Source And Designator:				
F-9 mil-m-38510				
Current Rating Per Characteristic:				
185.00 milliamperes reverse current, dc absolute				
Terminal Surface Treatment:				
Solder				
Product Name:				
And-or invert gate array				
Voltage Rating And Type Per Characteristic:				
-0.5 volts power source and 7.0 volts power source				
Time Rating Per Chacteristic:				
30.00 nanoseconds propagation delay time, high to low level output and 30.00 nanoseconds propagation delay time, low to high level				
output				
Memory Device Type:				

Pal

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Test	Data	Docum	ent
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96906-mil-std-883 standard (includes industry or association standards, individual manufactureer standards, etc.).

Terminal Type And Quantity:

20 flat leads

Shelf Life:

N/a

Unit Of Measure:

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Demilitarization:

Yes - demil/mli

Fiig:

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